

Three-Phase Brushless Motor Driver for Polygon Mirror Motors

Overview

The LB1876 is a driver for polygon mirror motors such as used in laser printers and similar equipment.

It incorporates all necessary circuitry (speed control + driver) on a single chip. Direct PWM drive enables drive with low power loss.

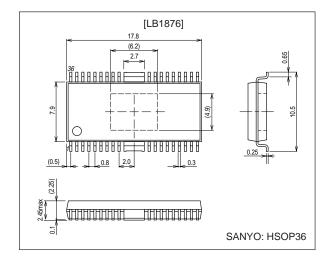
Functions and Features

- Three-phase bipolar drive
- Direct PWM drive technique
- Built-in lower side output diode
- Output current limiter
- Reference clock input circuit (FG frequency equivalent)
- · PLL speed control circuit
- Phase lock detector output (with masking function)
- Built-in protection circuitry includes current limiter, restraint protection, overheat protection, low-voltage protection, etc.
- Brake method switching circuit (free-run or reverse torque)
- 5V regulator output
- Power save function

Package Dimensions

unit: mm

3235A-HSOP36



Specifications

Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage 1	V _{CC} max		30	V
Maximum output current	I _O max	T ≤ 500 ms	2.5	Α
Allowable power dissipation 1	Pd max1	IC only	0.9	W
Allowable power dissipation 2	Pd max2	*With substrate	2.1	W
Operating temperature	Topr		-20 to +80	°C
Storage temperature	Tstg		-55 to +150	°C

^{*} Substrate: 114.3 × 76.1 × 1.6 mm³, glass epoxy

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Allowable Operating Ranges at $Ta=25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Power supply voltage range	V _{CC}		9.5 to 28	V
5 V regulated output current	IREG		0 to -20	mA
LD pin voltage	VLD		0 to 28	V
LD pin output current	ILD		0 to 15	mA
FGS pin voltage	VFGS		0 to 28	V
FGS pin output current	IFGS		0 to 10	mA

Electrical Characteristics at $Ta=25^{\circ}C,\,V_{CC}$ = VM = 24 V

$\begin{array}{ c c c c c c c } \hline Power supply current 1 & I_{CC} 1 & min & typ & max \\ \hline Power supply current 2 & I_{CC} 2 & Quiescent Current & 3.6 & 5.0 & mA \\ \hline [5V regulated output] \\ \hline Output voltage & VREG & 4.65 & 5.0 & 5.35 & V \\ \hline Voltage fluctuation & \Delta VREG1 & V_{CC} = 9.5 to 28 V & 50 & 100 & mV \\ \hline Load fluctuation & \Delta VREG2 & I_0 = -5 to -20 mA & 30 & 100 & mV \\ \hline Temperature coefficcient & \Delta VREG3 & Design target value & 0 & mV/C \\ \hline Output block] \\ \hline Output saturation voltage 1 & V_{OSA11} & I_0 = 1.0 A, V_O(SINK)+V_O(SOURCE) & 2.0 & 2.5 & V \\ \hline Output saturation voltage 2 & V_{OSA12} & I_0 = 2.0 A, V_O(SINK)+V_O(SOURCE) & 2.6 & 3.2 & V \\ \hline Output side control of cont$	Parameter	Cumbal	Conditions		Ratings		Unit
Power supply current 2	Farameter	Symbol	Conditions	min	typ	max	Offic
SV regulated output	Power supply current 1	I _{CC} 1			17	22	mA
Output voltage VREG VREG 4.65 5.0 5.35 V Voltage fluctuation ΔVREG1 0 = 5 to −20 mA 30 100 mV Load fluctuation ΔVREG2 0 = 5 to −20 mA 30 100 mV Temperature coefficient ΔVREG3 Design target value 0 mV/°C Output stauration voltage 1 Vosat1 10 = 1.0 A, Vo(SINK)+Vo(SOURCE) 2.0 2.5 V Output saturation voltage 2 Vosat2 10 = 2.0 A, Vo(SINK)+Vo(SOURCE) 2.6 3.2 V Output leak current Io/eak 100 µA 1.15 1.9 V Lower side diode forward voltage 1 VD1 ID = -1.0 A 1.2 1.5 V Lower side diode forward voltage 2 VD2 ID = -2.0 A 1.5 1.9 V Lower side diode forward voltage 2 VD2 ID = -2.0 A 1.5 1.9 V Lower side diode forward voltage 2 VD2 ID = -2.0 A 1.5 1.9 V Lower side diode forward voltage 2	Power supply current 2	I _{CC} 2	Quiescent Current		3.6	5.0	mA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	[5V regulated output]						
Load fluctuation	Output voltage	VREG		4.65	5.0	5.35	V
Temperature coefficient	Voltage fluctuation	ΔVREG1	V _{CC} = 9.5 to 28 V		50	100	mV
Courput block Output saturation voltage 1	Load fluctuation	ΔVREG2	$I_0 = -5 \text{ to } -20 \text{ mA}$		30	100	mV
Output saturation voltage 1 Vosat1 lo = 1.0 A, Vo(SINK)+Vo(SOURCE) 2.0 2.5 V Output saturation voltage 2 Vosat2 lo = 2.0 A, Vo(SINK)+Vo(SOURCE) 2.6 3.2 V Output leak current Ioleak 100 µA Lower side clode forward voltage 1 VD1 ID = 1.0 A 1.2 1.5 V Lower side clode forward voltage 2 VD2 ID = -2.0 A 1.5 1.9 V Ilyal amplifier block] VICM 0 1.5 1.9 V Imput bias current IHB -2 -0.5 µA Common mode input voltage range VICM 0 VREG-2.0 V Hysteresis width ΔV _{IN} (HA) 15 24 42 mV Input voltage L → H VSLH 12 mV mV mpU routage H → L VSHL -12 mV Input sensitivity Vn(KFGS) 0 VREG-2.0 V IpA V MV MV MV Imput sensitivity N MV MV MV <td>Temperature coefficcient</td> <td>ΔVREG3</td> <td>Design target value</td> <td></td> <td>0</td> <td></td> <td>mV/°C</td>	Temperature coefficcient	ΔVREG3	Design target value		0		mV/°C
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	[Output block]					'	-
Output leak current I _c jeak 100 μA Lower side diode forward voltage 1 VD1 ID = −1.0 A 1.2 1.5 V Lower side diode forward voltage 2 VD2 ID = −2.0 A 1.5 1.9 V Input bias current IHB −2 −0.5 μA Common mode input voltage range VICM 0 VREG-2.0 V Hall input sensitivity 80 mVP-Hysteresis width 4.2 mV Hysteresis width ΔV _{IN} (HA) 15 2.4 4.2 mV Input voltage L → H VSH 12 mV	Output saturation voltage 1	V _O sat1	$I_O = 1.0 \text{ A}, V_O(SINK) + V_O(SOURCE)$		2.0	2.5	V
Lower side diode forward voltage 1 VD1 ID = −1.0 A 1.2 1.5 V Lower side diode forward voltage 2 VD2 ID = −2.0 A 1.5 1.9 V Input bias current IHB −2 −0.5 µA Common mode input voltage range VICM 0 VREG-20 V Hall input sensitivity 80 mVp- Hysteresis width ΔV _{IN} (HA) 15 24 42 mV Hysteresis width ΔV _{IN} (HA) 15 24 42 mV Input voltage H → L VSHL −12 mV Input voltage H → L VSHL −12 mV Input voltage Hold input voltage range VICM(FGS) 0 VREG-2.0 V Input sensitivity Vin(FGS) 80 mVp- Hysteresis width ΔV _{IN} (FGS) 80 mVp- Hysteresis width ΔV _{IN} (FGS) 80 mVp- Hysteresis width ΔV _{IN} (FGS) 15 24 42 mV Input v	Output saturation voltage 2	V _O sat2	$I_O = 2.0 \text{ A}, V_O(\text{SINK}) + V_O(\text{SOURCE})$		2.6	3.2	V
$ \begin{array}{ c c c c c } \hline Lower side diode forward voltage 2 & VD2 & ID = -2.0 A & 1.5 & 1.9 & V \\ \hline [Hall amplifier block] & & & & & & & & & \\ \hline Input bias current & IHB & & -2 & -0.5 & \mu A \\ \hline Common mode input voltage range & VICM & 0 & VREG-2.0 & V \\ \hline Hall input sensitivity & 80 & mVPD- \\ \hline Hysteresis width & \Delta V_{IN}(HA) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH & 12 & mV \\ \hline Input voltage L \rightarrow H & VSLH & -12 & mV \\ \hline Input voltage L \rightarrow H & VSHL & -12 & mV \\ \hline Input bias current & IB(FGS) & -2 & -0.5 & \mu A \\ \hline Common mode input voltage range & VICM(FGS) & 0 & VREG-2.0 & V \\ \hline Input bias current & IB(FGS) & -2 & -0.5 & \mu A \\ \hline Common mode input voltage range & VICM(FGS) & 80 & mVPD- \\ \hline Hysteresis width & \Delta V_{IN}(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 24 & 42 & mV \\ \hline Input voltage L \rightarrow H & VSLH(FGS) & 15 & 2.8 & 3.1 & V \\ \hline Cutput Low level voltage & VOH(PWM) & 2.5 & 2.8 & 3.1 & V \\ \hline Cutput Low level voltage & VOL(PWM) & 1.05 & 1.27 & 1.50 & VPD \\ \hline FGS output] & 0 & 0.15 & 0.5 & V \\ \hline Cutput Low level voltage & VOL(FGS) & IFGS = 7 mA & 0.15 & 0.5 & V \\ \hline Cutput Low level voltage & VOL(FGS) & 0.75 & 0.9 & 1.1 & V \\ \hline Cutput Low level voltage & VOL(FGS) & 0.75 & 0.9 & 1.1 & V \\ \hline Cutput Low level voltage & VOL(CSD) & 0.75 & 0.9 & 1.1 & V \\ \hline Cutput Low level voltage & VOL(CSD) & 0.75 & 0.9 & 1.1 & V \\ \hline Cutput Low level voltage & VOL(CSD) & 0.75 & 0.9 & 1.1 & VPD \\ \hline External capacitor charge $	Output leak current	l _O leak				100	μA
Hall amplifier block Input bias current	Lower side diode forward voltage 1	VD1	ID = -1.0 A		1.2	1.5	V
Input bias current IHB	Lower side diode forward voltage 2	VD2	ID = -2.0 A		1.5	1.9	V
Common mode input voltage range VICM 0 VREG-20 V Hall input sensitivity 80 mVp— Hysteresis width ΔV _{IN} (HA) 15 24 42 mV Input voltage L → H VSLH 12 mV Input voltage H → L VSHL −12 mV Input tobias current IB(FGS) −2 −0.5 µA Common mode input voltage range VICM(FGS) 0 VREG-20 V Input sensitivity V _{IN} (FGS) 80 mVP— Hysteresis width ΔY _{MI} (FGS) 15 24 42 mV Input voltage L → H VSLH(FGS) 15 24 42 mV Input voltage B → L VSHL(FGS) 12 mV IPVM oscillator] 0 vSHL(FGS) −12 mV Output High level voltage VOL(PWM) 2.5 2.8 3.1 V Output High level voltage VOL(PWM) 1.2 1.5 1.8 V External capaci	[Hall amplifier block]						
Common mode input voltage range VICM 0 VREG-2.0 V Hall input sensitivity 80 mVp— Hysteresis width ΔV _{IN} (HA) 15 24 42 mV Input voltage L → H VSLH 12 mV Input voltage H → L VSHL −12 mV Input voltage H → L VSHL −2 −0.5 µA Common mode input voltage range VICM(FGS) 0 VREG-2.0 V Input sensitivity VIN(FGS) 80 mVP— Hysteresis width ΔV _M (FGS) 15 24 42 mV Input voltage L → H VSLH(FGS) 15 24 42 mV Input voltage B → L VSHL(FGS) 12 mV IPVM oscillator] 0 −12 mV Output High level voltage VOL(PWM) 2.5 2.8 3.1 V Output Low level voltage VOL(PWM) 1.2 1.5 1.8 V External capacitor charge current <	Input bias current	IHB		-2	-0.5		μA
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Common mode input voltage range	VICM		0		VREG - 2.0	<u> </u>
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$, , ,			80			mVp-p
$ \begin{array}{ c c c c c } \hline Input voltage $L \to H$ & VSLH & 12 & mV \\ \hline Input voltage $H \to L$ & VSHL & -12 & mV \\ \hline IFG/Schmitt block] & & & & & & & & & & & & & & & & & & &$	· · · · · · · · · · · · · · · · · · ·	ΔV _{IN} (HA)		15	24	42	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	•				12		
Input bias current IB(FGS) -2 -0.5 μA	· · · · · ·	VSHL			-12		mV
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$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	· · · · · · · · · · · · · · · · · · ·	IB(FGS)		-2	-0.5		uА
$\begin{array}{ c c c c c c }\hline & & & & & & & & & & & & & & & & & & &$	'					VREG - 2.0	'
Hysteresis width $\Delta V_{IN}(FGS)$ 15 24 42 mV Input voltage L → H VS.H.(FGS) 12 mV Input voltage H → L VS.H.(FGS) −12 mV [PWM oscillator] Output High level voltage VOH(PWM) 2.5 2.8 3.1 V Output Low level voltage VOL(PWM) 1.2 1.5 1.8 V External capacitor charge current ICHG VPWM = 2 V −125 −95 −75 μA Oscillator frequency f(PWM) C = 3000 pF 22 kHz Amplitude V(PWM) 1.05 1.27 1.50 Vp-p-p [FGS output] Output saturation voltage Vo_L(FGS) IFGS = 7 mA 0.15 0.5 V Output leak current IL(FGS) IL(FGS) 0.5 V Output High level voltage Vo_H(CSD) 2.65 3.0 3.3 V Output Low level voltage Vo_L(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-p	· • •	· ' '		80			mVp-p
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	· · · · · · · · · · · · · · · · · · ·	,			24	42	
Input voltage H → L VSHL(FGS) -12 mV	•				12		mV
PWM oscillator	· •	+ ' '			-12		<u> </u>
Output High level voltage VOH(PWM) 2.5 2.8 3.1 V Output Low level voltage VOL(PWM) 1.2 1.5 1.8 V External capacitor charge current ICHG VPWM = 2 V -125 -95 -75 μA Oscillator frequency f(PWM) C = 3000 pF 22 kHz Amplitude V(PWM) 1.05 1.27 1.50 Vp-p [FGS output] Output saturation voltage VoL(FGS) IFGS = 7 mA 0.15 0.5 V Output leak current IL(FGS) 10 μA [CSD oscillator] Output High level voltage VoH(CSD) 2.65 3.0 3.3 V Output Low level voltage VoL(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-p External capacitor charge current ICHG1 -13.5 -9 -5.5 μA	· •	- (/				1	
Output Low level voltage VOL(PWM) 1.2 1.5 1.8 V External capacitor charge current ICHG VPWM = 2 V -125 -95 -75 μA Oscillator frequency f(PWM) C = 3000 pF 22 kHz Amplitude V(PWM) 1.05 1.27 1.50 Vp-p [FGS output] Output saturation voltage VoL(FGS) IFGS = 7 mA 0.15 0.5 V Output leak current IL(FGS) 10 μA [CSD oscillator] Output High level voltage VoH(CSD) 2.65 3.0 3.3 V Output Low level voltage VoL(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-p External capacitor charge current ICHG1 -13.5 -9 -5.5 μA	· · · · · · · · · · · · · · · · · · ·	VOH(PWM)		2.5	2.8	3.1	V
External capacitor charge current ICHG VPWM = 2 V -125 -95 -75 μA Oscillator frequency f(PWM) C = 3000 pF 22 kHz Amplitude V(PWM) 1.05 1.27 1.50 Vp-p [FGS output] Output saturation voltage Vo_L(FGS) IFGS = 7 mA 0.15 0.5 V Output leak current IL(FGS) 10 μA [CSD oscillator] Output High level voltage VoH(CSD) 2.65 3.0 3.3 V Output Low level voltage VoL(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-p External capacitor charge current ICHG1 -13.5 -9 -5.5 μA							-
Oscillator frequency f(PWM) C = 3000 pF 22 kHz Amplitude V(PWM) 1.05 1.27 1.50 Vp-p [FGS output] Output saturation voltage V _O L(FGS) IFGS = 7 mA 0.15 0.5 V Output leak current IL(FGS) 10 μA [CSD oscillator] Output High level voltage V _O H(CSD) 2.65 3.0 3.3 V Output Low level voltage V _O L(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-p External capacitor charge current ICHG1 -13.5 -9 -5.5 μA			VPWM = 2 V				
Amplitude V(PWM) 1.05 1.27 1.50 Vp-p [FGS output] Output saturation voltage VoL(FGS) IFGS = 7 mA 0.15 0.5 V Output leak current IL(FGS) 10 μA [CSD oscillator] Output High level voltage VoH(CSD) 2.65 3.0 3.3 V Output Low level voltage VoL(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-p External capacitor charge current ICHG1 -13.5 -9 -5.5 μA				120			
FGS output Output saturation voltage	. ,	<u> </u>	- 3333 р.	1.05		1.50	
	<u>'</u>	*(. *****)		1100			.,,,
Output leak current IL(FGS) 10 μA [CSD oscillator] Output High level voltage VoH(CSD) 2.65 3.0 3.3 V Output Low level voltage VoL(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-F External capacitor charge current ICHG1 -13.5 -9 -5.5 μA		Vol.(FGS)	IFGS = 7 mA		0.15	0.5	V
CSD oscillator	-				3.10		
Output High level voltage V _O H(CSD) 2.65 3.0 3.3 V Output Low level voltage V _O L(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-p External capacitor charge current ICHG1 -13.5 -9 -5.5 μA	· ·	IL(I OO)				10	μΛ
Output Low level voltage V _O L(CSD) 0.75 0.9 1.1 V Amplitude V(CSD) 1.75 2.1 2.3 Vp-ρ External capacitor charge current ICHG1 -13.5 -9 -5.5 μA	-	VoH(CSD)		2.65	3.0	2.2	\/
Amplitude V(CSD) 1.75 2.1 2.3 Vp-p External capacitor charge current ICHG1 -13.5 -9 -5.5 μA		+ - ' '					
External capacitor charge current ICHG1 -13.5 -9 -5.5 μA	<u> </u>	+ - ' '					-
	<u>'</u>						
Балентан сарасног изонатуе синет 10ПО2 5.5 9 13.5 µA	·						
Oscillator frequency $f(CSD)$ $C = 0.068 \mu F$ 30 Hz			C = 0.068 HE	5.5		13.5	· ·

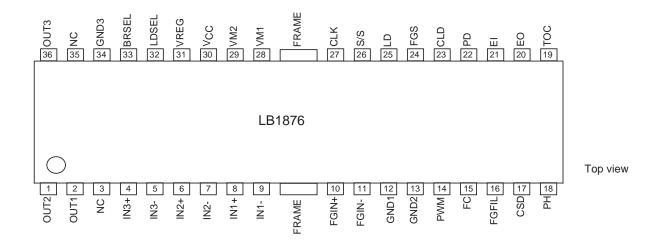
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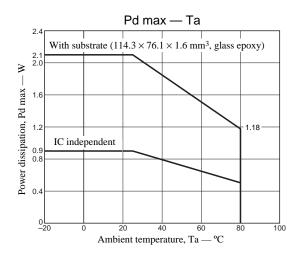
Parameter	Symbol	Conditions		Ratings		Unit
i didiffetei	Symbol	Conditions	min	typ	max	Offic
[Phase comparator output]						
Output High level voltage	VPDH	$I_0H = -100 \mu A$	VREG-0.2	VREG-0.1		V
Output Low level voltage	VPDL	I _O H = 100 μA		0.2	0.3	V
Output source current	IPD+	VPD = VREG/2			-0.5	mA
Output sink current	IPD-	VPD = VREG/2	1.5			mA
[Phase lock detector output]						
Output saturation voltage	V _O L(LD)	ILD = 10 mA		0.15	0.5	V
Output leak current	IL(LD)	$V_O = V_{CC}$			10	μΑ
[ERR amplifier]						
Input offset voltage	V _I O(ER)	Design target value	-10		+10	mV
Input bias current	I _B (ER)		-1		+1	μΑ
Ouput High level voltage	V _O H(ER)	I _O H = -500 μA	VREG-1.2	VREG-0.9		V
Ouput Low level voltage	V _O L(ER)	I _O L = 500 μA		0.9	1.2	V
DC bias level	VB(ER)		-5%	VREG/2	+5%	V
[Current limiter]	, ,					
Drive gain 1	GDF1	in phase lock mode	0.4	0.5	0.6	times
Drive gain 2	GDF2	in unlock mode	0.8	1.0	1.2	times
Limiter voltage	VRF	Vcc - V _M	0.45	0.5	0.55	V
[Thermal shutdown operation]	1	CC - IVI	1 0.10	1 3.0	2.00	
Termal shutdown operating temperature	TSD	Design target value (junction temperature)	150	180		°C
Hysteresis width	ΔTSD	Design target value (junction temperature)	130	40		°C
[Low voltage protection]	ДТОВ	Design target value (junction temperature)		40		
Operating voltage	VSD	I	8.1	8.5	8.9	V
· · · · · · · · · · · · · · · · · · ·						V
Hysteresis [CLD circuit]	ΔVSD		0.2	0.35	0.5	V
[CLD circuit]	101.0			4.0		
External capacitor charge current	ICLD		-6	-4.3	-3	V
Operating voltage	VH(CLD)		3.25	3.5	3.75	V
[CLK pin]		I				
External input frequency	fl(CKIN)		0.1		10	kHz
High level input voltage	V _I H(CKIN)		3.5		VREG	V
Low level input voltage	V _I L(CKIN)		0		1.5	V
Input open voltage	V _I O(CKIN)		VREG-0.5		VREG	V
Hysteresis width	V _I S(CKIN)		0.35	0.5	0.65	V
High level input current	I _I H(CKIN)	VCKIN = VREG	-10	0	+10	μΑ
Low level input current	I _I L(CKIN)	VCKIN = 0 V	-280	-210		μΑ
[S/S pin]						
High level input voltage	V _I H(SS)		3.5		VREG	V
Low level input voltage	V _I L(SS)		0		1.5	V
Input open voltage	V _I O(SS)		VREG-0.5		VREG	V
Hysteresis width	V _I S(SS)		0.35	0.5	0.65	V
High level input current	I _I H(SS)	VS/S = VREG	-10	0	+10	μA
Low level input current	I _I L(SS)	VS/S = 0 V	-280	-210		μΑ
[LDSEL pin]	1	1				-
High level input voltage	V _I H(LD _{SEL})		3.5		VREG	V
Low level input voltage	V _I L(LD _{SEL})		0		1.5	V
Input open voltage	V _I O(LD _{SEL})		VREG-0.5		VREG	V
High level input current	I _I H(LD _{SEL})	V _{LDSEL} = VREG	-10	0	10	μA
Low level input current	I _I L(LD _{SEL})	V _{LDSEL} = 0 V	-280	-210		μΑ
[BRSEL pin]	1-(25EL)	LDOLL -				I L.,
High level input voltage	V _I H(BR _{SEL})		3.5		VREG	V
Low level input voltage	V _I L(BR _{SEL})		0		1.5	V
	V _I L(BR _{SEL})		VREG-0.5		VREG	V
Input open voltage			_			-
High level input current	I _I H(BR _{SEL})	V _{LDSEL} = VREG	-10	0	10	μA

Three-phase logic truth table (IN = "H" indicates the IN+ > IN- condition)

IN1	IN2	IN3	OUT1	OUT2	OUT3
Н	L	Н	L	Н	М
Н	L	L	L	М	Н
Н	Н	L	М	L	Н
L	Н	L	Н	L	М
L	Н	Н	Н	М	L
L	L	Н	М	Н	L

Pin Assignment

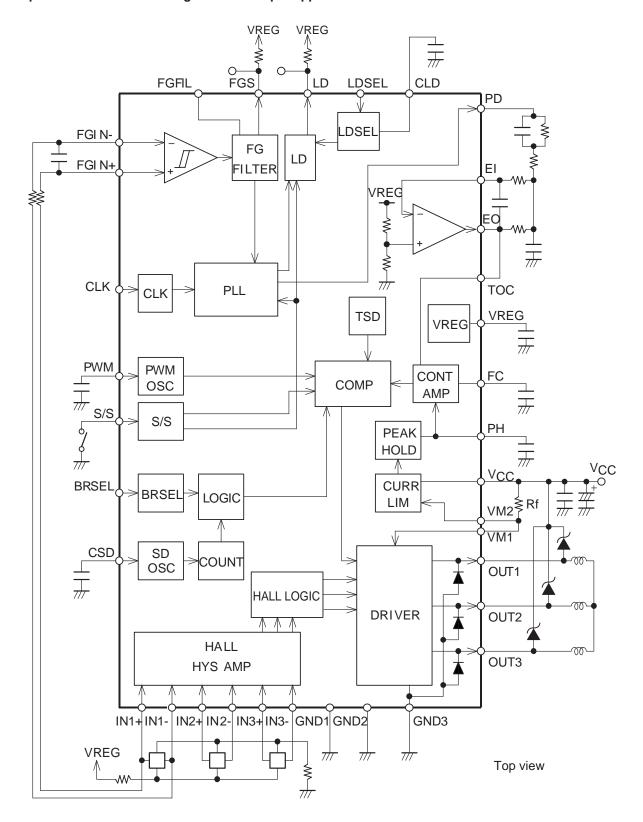




Pin Description

Pin name	Pin number	Function			
OUT1	2	Output pins.			
OUT2	1	PWM controls duty cycle ratio by lower transistors.			
OUT3	36	Connect Schottky diode between these pins and VCC.			
IN1+, IN1-	8, 9				
IN2+, IN2-	6, 7	Hall input pins for each phase. Logic High indicates VIN+ > VIN			
IN3+, IN3-	4, 5	Logic riigh indicates viiv+ > viiv			
FG IN+	10	FG comparator non-inverting input.			
FG IN-	11	FG comparator inverting input.			
GND1	12	Control circuit ground.			
GND2	13	Sub-ground.			
PWM	14	PWM oscillation frequency setting pin. Connect to ground via capacitor.			
FC	15	Current control circuit frequency characteristics compensation pin. Connect to ground via capacitor.			
FGFIL	16	FG filter pin. Connect to ground via capacitor if noise in FG signal is a problem.			
CSD	17	Restraint protection circuit operating time setting pin/reset pulse setting pin. Connect to ground via capacitor. If the protection circuit is not to be used, connect a resistor in parallel with capacitor.			
PH	18	RF waveform smoothing pin. Connect to ground via capacitor.			
тос	19	Torque specifying input pin. Normally connected to EO pin. When TOC potential falls, ON duty cycle ratio of lower side output transistors changes and torque increases.			
EO	20	Error amplifier output.			
El	21	Error amplifier input.			
PD	22	Phase comparator output pin. Phase deviation is output as a duty cycle change of the pulse.			
CLD	23	Phase lock signal masking time setting pin. Connect to ground via capacitor. Leave open if masking is not required.			
FGS	24	FG Schmitt output (open collector output).			
LD	25	Phase lock detector output (open collector output). Goes ON when PLL is locked.			
S/S	26	Start/stop input. Low: Start; High or Open: Stop.			
CLK	27	Clock input. 10 kHz max.			
VM1	28	Output block power supply. Short to VM2 for use.			
VM2	29	Output current detector pin. Connect to VCC via low resistor. Set to maximum output current IOUT = 0.5/Rf.			
VCC	30	Power supply pin. Connect to ground via capacitor to prevent noise.			
VREG	31	5V regulator output pin (control circuit power supply). Connect to ground via capacitor to stabilize operation.			
LDSEL	32	Phase lock signal masking switching pin. When "Low", the unlock signal (short "High" signal of LD output) is masked. When "High" or Open, the lock signal (short "Low" signal of LD output) is masked.			
BRSEL	33	Braking method select pin. "Low" selects reverse torque control and "High" or Open selects free-run. When reverse torque is controlled, lower side output transistors require external SBD.			
GND3	34	Output circuit ground.			
FRAME	_	The FRAME pin is connected internally to the metal frame at the base of the IC. Electrically, both the FRAME pin and the metal frame are left open. To improve thermal dissipation, provide a corresponding land on the PCB and solder the FRAME pin to that land.			
NC	3, 35	Not connected internally. Can be used for wiring.			
		1			

Equivalent Circuit Block Diagram and Sample Application Circuit



Pin Descriptions

Pin No.	Symbol	Description	Equivalent circuit
2 1 36	OUT1 OUT2 OUT3	Motor drive output. Connect Schottky diodes between the outputs and VCC.	VCC VM2 (29) VM1 (28)
34	GND3	Output block ground Output block power supply and output current	1)(2)(36)
28 29	VM1 VM2	detection Connect low-resistance resistors Rf between these pins and VCC. The output current is limited to the current value set by IOUT = VREF/Rf.	34
3 35	NC NC	Since these are not connected internally, they can be used for wiring.	
8 9 6 7 4 5	IN1+ IN1- IN2+ IN2- IN3+ IN3-	Hall device inputs These inputs return a high level when IN+ > IN- and a low level when IN- > IN+. A Hall signal amplitude of at least 100 mV p-p (differential) is desirable. Insert a capacitor between IN+ and IN- if noise on the Hall signal is a problem.	4 6 8 300Ω 300Ω 5 7 9
10 11	FGIN1+ FGIN1-	FG inputs If noise on the FG signal is a problem, insert either a capacitor or a filter consisting of a capacitor and a resistor.	VREG 10 300Ω 10 300Ω 11 11
12	GND1	Control circuit block ground	
13	GND2	Sub-ground	

Pin No.	Symbol	Description	Equivalent circuit
14	PWM	Sets the PWM oscillator frequency. Connect a capacitor between this pin and ground. A capacitance of 1800 pF for C sets the frequency to approximately 37 kHz.	VREG 200Ω 14 2KΩ \$ 14
15	FC	Current control circuit frequency characteristics correction. Insert a capacitor (on the order of 0.01 to 0.1 µF) between this pin and ground. The output duty is determined by the ratio of the voltage on this pin and the PWM oscillator waveform.	VREG 300Ω 15
16	FGFIL	FG filter connection If noise on the FG signal is a problem, insert a capacitor (under about 2200 pF) between this pin and ground.	VREG 16
17	CSD	Sets the operating time of the constraint protection circuit and also sets the initial reset pulse. A protection operating time of about 8 seconds can be set by connecting a capacitor (about $0.068~\mu\text{F}$) between this pin and ground. If the protection circuit is not used, connect a capacitor and resistor (about $4700~\text{pF}$, $220~\text{k}\Omega$) in parallel between this pin and ground.	VREG 300Ω 17
18	РН	RF smoothing If noise on the RF signal is a problem, insert a capacitor between this pin and ground.	VREG 500Ω 18

Pin No.	Symbol	Description	Equivalent circuit
19	тос	Torque command voltage input Normally, this pin is connected to the EO pin. When the TOC voltage falls, the on duty of the lower side transistor increases.	VREG 300Ω 19
20	EO	Error amplifier output	VREG (20)
21	EI	Error amplifier input	VREG 300Ω 21
22	PD	Phase comparator output The phase error is converted to a pulse duty and output from this pin.	VREG 300Ω W (22)
23	CLD	Phase lock signal mask time setting A mask time of about 90 ms can be set by inserting a capacitor (about 0.1 µF) between this pin and ground. Leave this pin open if there is no need to mask.	VREG 300Ω W 23

Pin No.	Symbol	Description	Equivalent circuit
24	FGS	FG Schmitt output	VREG (24)
25	LD	Phase lock detection output Turns on (goes low) when phase lock is detected.	VREG 25
26	S/S	Start/stop control Low: 0 to 1.5 V High: 3.5 V to VREG Hysteresis: About 0.5 V Apply a low level to start; this pin goes high when open.	VREG 22kΩ ₹ 22kΩ ₹ 26
27	CLK	Clock input Low: 0 to 1.5 V High: 3.5 V to VREG Hysteresis: About 0.5 V fCLK = 10 kHz maximum If there is noise on the clock signal, remove that noise with a capacitor.	VREG 22 kΩ 22 kΩ 27 27
30	V _{cc}	Power supply Insert a capacitor between this pin and ground to prevent noise from entering the IC. (Use a value of 20 or 30 µF or higher.)	
31	VREG	Stabilized power supply output (5 V output) Insert a capacitor between this pin and ground for stabilization. (About 0.1 µF.)	Continued on next page

Pin No.	Symbol	Description	Equivalent circuit
32	LDSEL	Phase lock signal mask switching Low: 0 to 1.5 V High: 3.5 V to VREG When open, this pin goes to the high level. When low, transient unlock signals (short high-level periods on the LD output) are masked, and when high, transient lock signals (short low-level periods on the LD output) are masked.	VREG 30 kΩ 2kΩ 32
33	BRSEL	Braking control Low: 0 to 1.5 V High: 3.5 V to VREG When open, this pin goes to the high level. When low, reverse torque control is applied and when high, the circuit operates in free-running mode. An external Schottky barrier diode is required on the low side output when reverse torque control is applied.	VREG 30 kΩ \$ 2kΩ 333
	FREME	This pin must be left open.	

LB1876 Overview

1. Speed control circuit

This IC provides high-precision, low-jitter, and stable motor rotation since it adopts a PLL speed control technique. This PLL circuit compares the phases of the edges on the CLK signal (falling edges) and the FG signal (falling edges on the FG_{IN}+.FGS output) and controls the speed using that error output.

The FG servo frequency during control operation is the same as the clock frequency.

$$f_{FG}(servo) = fC_{LK}$$

2. Output drive circuit

To reduce power loss in the output, this IC adopts a direct PWM drive technique. The output transistors are always saturated when on, and the motor drive power is controlled by changing the output on duty. Since the lower side transistor is used for the output PWM switching, Schottky diodes must be inserted between the outputs and V_{CC} . (This is because if the diodes used do not have a short reverse recovery time, instantaneous through currents will flow when the lower side transistor turns on.)

The diodes between the outputs and ground are built in. However, if problems (such as waveform disruption during lower side kickback) occur for large output currents, attach external rectifying diodes or Schottky diodes. If reverse control mode is selected for braking and problems such as incorrect operation or excess heat generation due to the reverse recovery time of the lower side diode causes a problem, add an external Schottky diode.

3. Current control circuit

The current control circuit controls the current (limits the peak current) to the current determined by $I = V_{RF}/Rf$ ($V_{RF} = 0.5 \text{ V}$ typ., Rf: current detection resistor). The limiting operation consists of reducing the output on duty to suppress the current.

The current control circuit detects the diode reverse recovery current due to the PWM operation, and has an operating delay (about 3 µs) to prevent incorrect current limiting operation. If the motor coils have a relatively low resistance, or relatively low inductance, the changes in current flow at startup (the state where the motor presents no back electromotive force) will be rapid. As a result, the current limiter may operate at currents in excess of the set current due to this delay. In such cases, the current limit value must be set so as to take the current increase due to the delay into account.

4. Power saving circuit

This IC goes to the power saving state, which reduces power consumption, in the stopped state. Power is reduced in the power saving state by cutting the bias current to most of the circuit blocks in the IC. However, the 5 V regulator circuit does operate and provide its output in the power saving state.

5. Reference clock

The externally input clock signal must be free of chattering and other noise. The input circuit does have hysteresis, but if problems occur, the clock signal must be input through a capacitor or other noise reduction circuit.

If the IC is set to the start state with no reference clock input, and if the constraint protection circuit is operated, after the motor rotates a certain amount, the drive will be turned off. However, if the constraint protection circuit is not operated, and furthermore, if reverse control mode is selected during braking, the motor will run backwards at increasing speed. A workaround will be required in this case. (This problem occurs because the constraint protection circuit oscillator signal is used for clock cutoff protection.)

6. PWM frequency

The PWM frequency is determined by the capacitor C (F) connected to the PWM pin.

$$fPW \approx 1/(15000 \times C)$$

If an 1800 pF capacitor is used, the frequency will be about 37 kHz. If the PWM frequency is too low, the motor will emit audible switching noise, and if it is too high, the power loss will increase. A frequency in the range 15 to 50 kHz is desirable. The capacitor ground must be connected as close as possible to the IC control block ground (the GND1 pin) to minimize the influence of the output on this circuit.

7. Hall sensor input signals

Input signals with amplitudes greater than the input circuit hysteresis (42 mV maximum) must be provided to the Hall inputs. Input amplitudes of over 100 mV are desirable to minimize the influence of noise. If the output waveform is disturbed by noise (at phase switching), insert capacitors across the input to prevent this.

8. FG input signal

Normally, one of the Hall sensor signals is input as an FG signal. If noise on the FG input is a problem, insert either a capacitor or a filter consisting of a capacitor and a resistor. Although it is possible to exclude noise from the FG signal by inserting a capacitor between the FGFIL pin and ground, if this pin's waveform is smoothed excessively, the circuit may not be able to operate normally. Therefore, if a capacitor is used here, its value must be held to under 2200 pF. If the position of the capacitor's ground lead is inappropriate, problems due to noise may become more likely to occur. Select the position carefully.

9. Constraint protection circuit

This IC includes a built-in constraint protection circuit to protect the IC and the motor during motor constraint. In the start state, when the LD output is high for a fixed period (the unlocked state), the lower side transistor turns off. The time is set by the capacitor connected to the CSD pin.

Set time (seconds)
$$\approx 120 \times C (\mu F)$$

If a $0.068~\mu F$ capacitor is used, the protection time will be about 8 seconds. The set time must have a value that provides an adequate margin relative to the motor start time. The protection circuit does not operate during braking implemented by switching the clock frequency. Either switch to the stop state or turn off the power and restart to clear the constraint protection state.

Since the CSD pin also functions as the initial reset pulse generation pin, if connected to ground the logic circuits will be reset and speed control operation will not be possible. Therefore, if constraint protection is not used, connect CSD to ground through a resistor of about 220 k Ω and a capacitor of about 4700 pF in parallel.

10. Phase lock signal

(1) Phase lock range

Since this IC does not have a counter in the speed control system, the speed error range in the phase locked state cannot be determined solely by the IC's characteristics. (This is because of the influence of the acceleration of the changes in the FG frequency.) If it is necessary to stipulate this for the motor, it will be necessary to measure this with the actual motor. Since it is easier for speed errors to occur in the state where the FG acceleration is large, the largest speed errors are thought to occur during lock pull-in at startup and when unlocked due to clock frequency switching.

(2) Phase lock signal mask function

When the LDSEL pin is set high or left open, transient lock signals (short low-level periods on the LD output) is masked. This function masks short low-level periods due to hunting during pull-in and allows a stable lock signal to be output. However, the lock signal is delayed by amount of masking time.

When the LDSEL pin is set low, transient unlock signals (short high-level periods on the LD output) is masked. This function prevents short period high-level signals from being output.

The mask time is set with the capacitor connected between the CLD pin and ground.

Mask time (seconds)
$$\approx 0.9 \times C (\mu F)$$

A mask time of about 90 ms can be set by using a capacitor of about 0.1 µF. If complete masking is required, the mask time must be set large enough to provide ample margin. If masking is not required, leave the CLD pin open.

11. Power supply stabilization

Since this IC provides a large output current and adopts a switching drive technique, it can easily disrupt the power supply line voltage. Therefore, capacitors with ample capacitance must be inserted between the VCC pins and ground.

If reverse control mode is selected during braking, the circuit will return current to the power supply. This means that the power supply lines are even more susceptible to disruption. Since the power supply is most easily influenced during lock pull-in at high motor speeds, this case requires particular care. Select capacitor values that are fully adequate for this case.

If diodes are inserted in the power supply lines to prevent damage if the power supply is connected with reverse polarity, the power supply voltage will be even more susceptible to disruption, and even larger capacitors must be used.

12. V_{REG} stabilization

Insert a capacitor of at least $0.1 \mu F$ to stabilize VREG, which is the control circuit power supply. The capacitor ground must be connected as close as possible to the IC control block ground (the GND1 pin).

13. Error amplifier circuit components

Locate the error amplifier components as close to the IC as possible to minimize the influence of noise on this circuit. Locate this circuit as far from the motor as possible.

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